

Title (en)

Method of manufacturing ferroelectric layer and method of manufacturing electronic device

Title (de)

Verfahren zur Herstellung einer ferroelektrischen Schicht und Verfahren zur Herstellung einer elektronischen Anordnung

Title (fr)

Procédé de fabrication d'une couche ferroélectrique et procédé de fabrication d'un dispositif électronique

Publication

EP 1729333 A3 20080123 (EN)

Application

EP 06009304 A 20060505

Priority

JP 2005162542 A 20050602

Abstract (en)

[origin: EP1729333A2] A method of manufacturing a ferroelectric layer, including: forming a first ferroelectric layer above a base by a vapor phase method; and forming a second ferroelectric layer above the first ferroelectric layer by a liquid phase method.

IPC 8 full level

H01L 21/316 (2006.01); **B41J 2/045** (2006.01); **B41J 2/055** (2006.01); **B41J 2/135** (2006.01); **B41J 2/14** (2006.01); **B41J 2/16** (2006.01); **H01L 21/8246** (2006.01); **H01L 27/105** (2006.01); **H10N 30/076** (2023.01); **H10N 30/077** (2023.01); **H10N 30/079** (2023.01); **H10N 30/093** (2023.01); **H10N 30/20** (2023.01); **H10N 30/85** (2023.01); **H10N 30/853** (2023.01); **H01L 21/02** (2006.01)

CPC (source: EP KR US)

H01L 21/02197 (2013.01 - KR US); **H01L 21/022** (2013.01 - EP KR US); **H01L 21/02205** (2013.01 - EP KR US); **H01L 21/02271** (2013.01 - KR US); **H01L 21/02282** (2013.01 - KR US); **H01L 21/31691** (2013.01 - US); **H01L 27/105** (2013.01 - KR); **H01L 28/56** (2013.01 - EP US); **H10N 30/076** (2023.02 - EP US); **H10N 30/078** (2023.02 - EP US); **H01L 21/02197** (2013.01 - EP); **H01L 21/02271** (2013.01 - EP); **H01L 21/02282** (2013.01 - EP); **H10N 30/8554** (2023.02 - EP US)

Citation (search report)

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